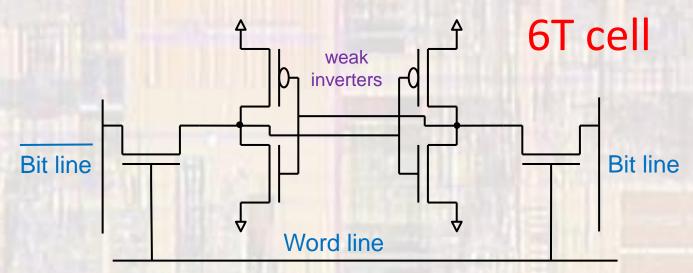
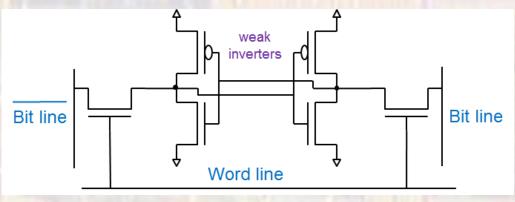
# SRAM

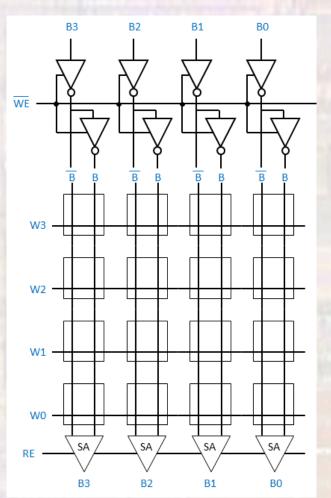
Last updated 2/5/24

- SRAM Static Random Access Memory
  - · Memory cell (1 bit) is based on a feedback circuit
  - Bit value is retained as long as power is maintained
  - Fastest read/write (R/W)
  - Highest power
  - Lowest density
  - Used in caches and small data memories

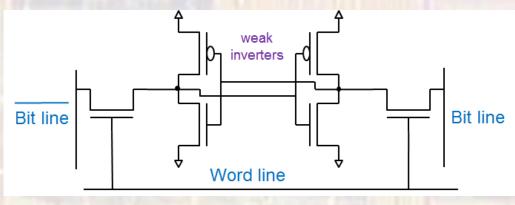


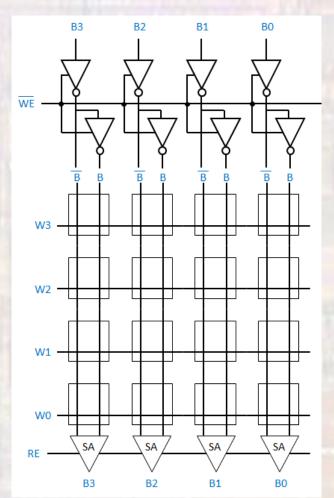
- SRAM Static Random Access Memory
  - Write
    - All Word lines low
    - Read Enable (RE) disabled (low)
    - Place B0, B1, B2, B3 on inputs
    - Pull write enable bar (WE) low
    - Strobe the desired word line high
    - Bit lines override the bit cell inverters and store the new value in the cell





- SRAM Static Random Access Memory
  - Read
    - All Word lines low
    - Write enable bar (WE) high
      - inverters tristated
    - Read Enable (RE) high
    - Strobe the desired word line high
    - Bit cell inverters drive the bit lines and sense amplifiers read the value





- SRAM Static Random Access Memory
  - Sense Amplifiers

